

## Product Summary

$V_{(BR)DSS}$	$R_{DS(ON)}$ max	$I_D$ max $T_A = 25^\circ\text{C}$
-20V	150m $\Omega$ @ $V_{GS} = -4.5\text{V}$	-1.5A
	200m $\Omega$ @ $V_{GS} = -2.5\text{V}$	-1A
	240m $\Omega$ @ $V_{GS} = -1.8\text{V}$	-0.9A

## Description and Applications

This MOSFET is designed to minimize the on-state resistance ( $R_{DS(on)}$ ) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

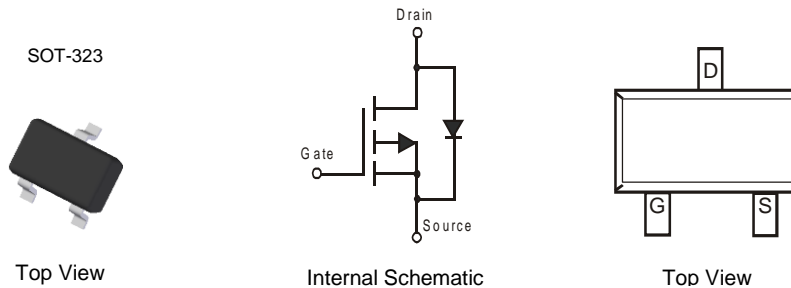
- Backlighting
- Power Management Functions
- DC-DC Converters

## Features

- Low On-Resistance
- Very Low Gate Threshold Voltage  $V_{GS(th)} \leq 1\text{V}$
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**
- **PPAP Capable (Note 4)**

## Mechanical Data

- Case: SOT-323
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals Connections: See Diagram Below
- Terminals: Finish — Matte Tin Annealed over Alloy 42 Leadframe. Solderable per MIL-STD-202, Method 208
- Weight: 0.006 grams (Approximate)

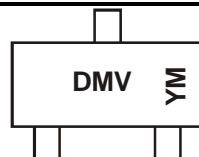


## Ordering Information (Note 5)

Part Number	Case	Packaging
DMP2240UWQ-7	SOT-323	3,000/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
  2. See [http://www.diodes.com/quality/lead\\_free.html](http://www.diodes.com/quality/lead_free.html) for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified. For more information, please refer to [http://www.diodes.com/quality/product\\_grade\\_definitions/](http://www.diodes.com/quality/product_grade_definitions/).
  5. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

## Marking Information



DMV = Product Type Marking Code  
 YM = Date Code Marking  
 Y = Year (ex: B = 2014)  
 M = Month (ex: 9 = September)

### Date Code Key

Year	2014	2015	2016	2017	2018	2019	2020	2021
Code	B	C	D	E	F	G	H	I

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

**Maximum Ratings** (@ $T_A = +25^\circ\text{C}$  unless otherwise specified.)

Characteristic	Symbol	Value	Units
Drain-Source Voltage	$V_{DSS}$	-20	V
Gate-Source Voltage	$V_{GSS}$	$\pm 12$	V
Drain Current (Note 6)	$I_D$	$T_A = +25^\circ\text{C}$	-1.5
		$T_A = +70^\circ\text{C}$	-1.0
Pulsed Drain Current	$I_{DM}$	-5	A

**Thermal Characteristics**

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 6)	$P_D$	250	mW
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	500	$^\circ\text{C/W}$
Operating and Storage Temperature Range	$T_J, T_{STG}$	-55 to +150	$^\circ\text{C}$

**Electrical Characteristics** (@ $T_A = +25^\circ\text{C}$  unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 7)</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	-20	—	—	V	$V_{GS} = 0V, I_D = -250\mu\text{A}$
Zero Gate Voltage Drain Current	$I_{DSS}$	$T_J = +25^\circ\text{C}$	—	-1.0	$\mu\text{A}$	$V_{DS} = -20V, V_{GS} = 0V$
		$T_J = +125^\circ\text{C}$	—	-5.0		
Gate-Source Leakage	$I_{GSS}$	—	—	$\pm 100$	nA	$V_{GS} = \pm 12V, V_{DS} = 0V$
<b>ON CHARACTERISTICS (Note 7)</b>						
Gate Threshold Voltage	$V_{GS(th)}$	-0.45	—	-1.0	V	$V_{DS} = V_{GS}, I_D = -250\mu\text{A}$
Static Drain-Source On-Resistance	$R_{DS(on)}$	—	92	150	m $\Omega$	$V_{GS} = -4.5V, I_D = -2.0A$
		—	134	200		$V_{GS} = -2.5V, I_D = -1.5A$
		—	180	240		$V_{GS} = -1.8V, I_D = -0.5A$
Forward Transconductance	$g_{FS}$	—	3.1	—	S	$V_{DS} = -10V, I_D = -810\text{mA}$
Diode Forward Voltage (Note 7)	$V_{SD}$	—	—	-0.9	V	$V_{GS} = 0V, I_S = -0.5A$
<b>DYNAMIC CHARACTERISTICS</b>						
Input Capacitance	$C_{iss}$	—	320	—	pF	$V_{DS} = -16V, V_{GS} = 0V$ $f = 1.0\text{MHz}$
Output Capacitance	$C_{oss}$	—	80	—	pF	
Reverse Transfer Capacitance	$C_{rss}$	—	60	—	pF	
Turn-On Delay Time	$t_{D(on)}$	—	12.5	—	ns	$V_{DS} = -10V, V_{GS} = -4.5V,$ $R_L = 10\Omega, R_G = 1.0\Omega$
Turn-On Rise Time	$t_r$	—	10.3	—	ns	
Turn-Off Delay Time	$t_{D(off)}$	—	46.5	—	ns	
Turn-Off Fall Time	$t_f$	—	22.2	—	ns	

Notes: 6. Device mounted on FR-4 substrate PC board, 2oz. Copper, with minimum recommended pad layout.  
7. Short duration pulse test used to minimize self-heating effect.

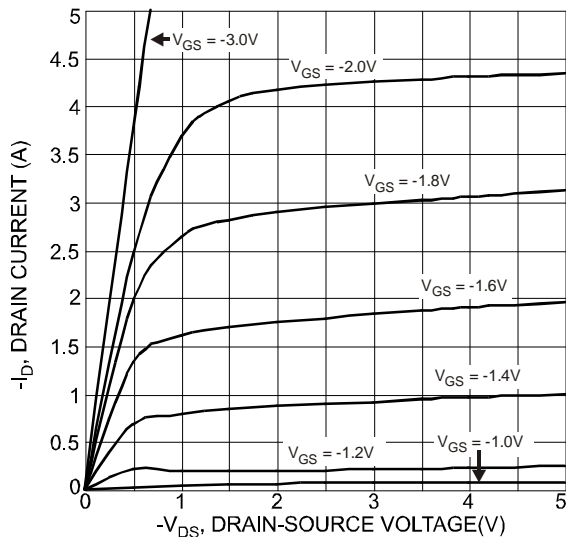


Fig. 1 Typical Output Characteristics

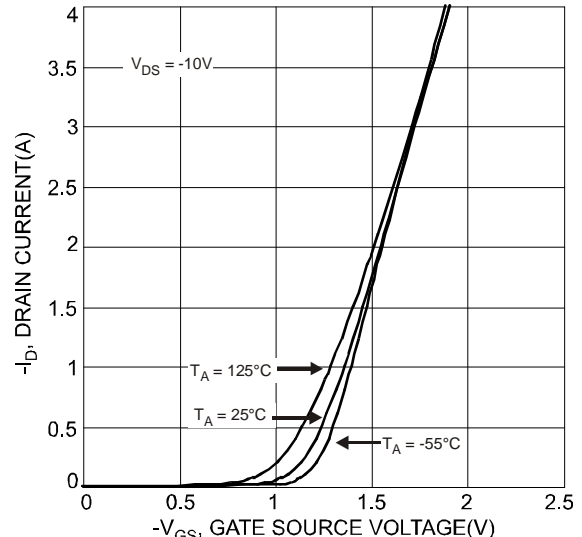


Fig. 2 Typical Transfer Characteristics

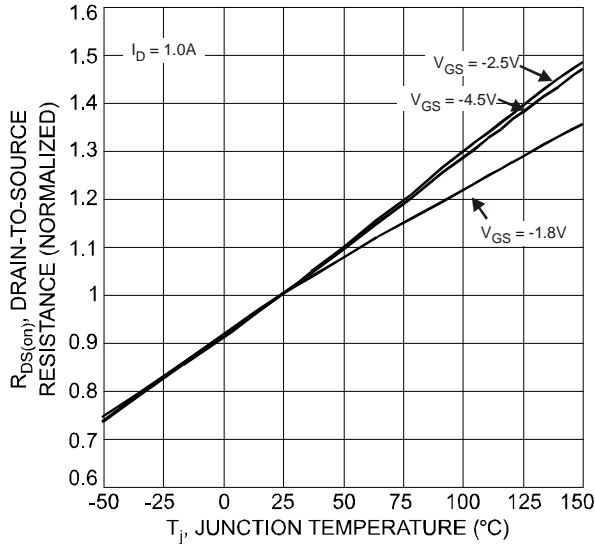


Fig. 3 On-Resistance Variation with Temperature

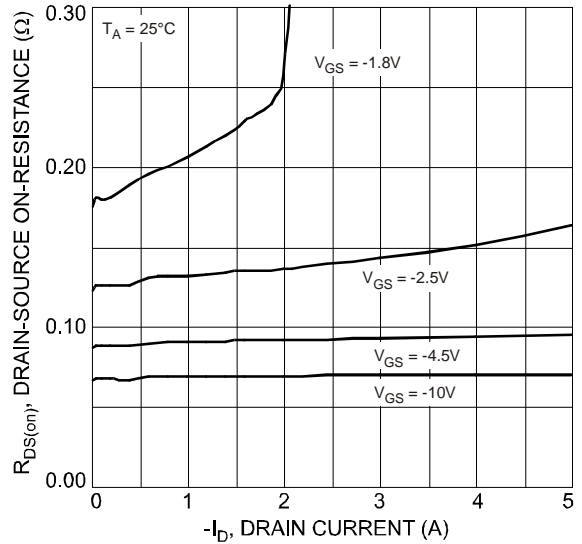


Fig. 4 On-Resistance vs Drain Current and Gate Voltage

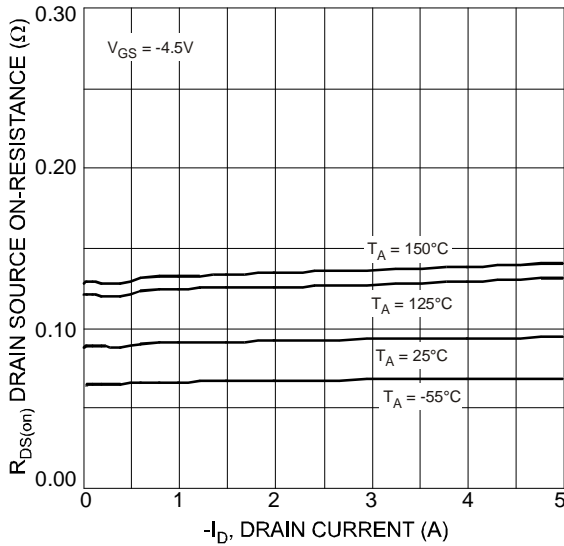


Fig. 5 Drain-Source On-Resistance Vs. Drain Current and Temperature

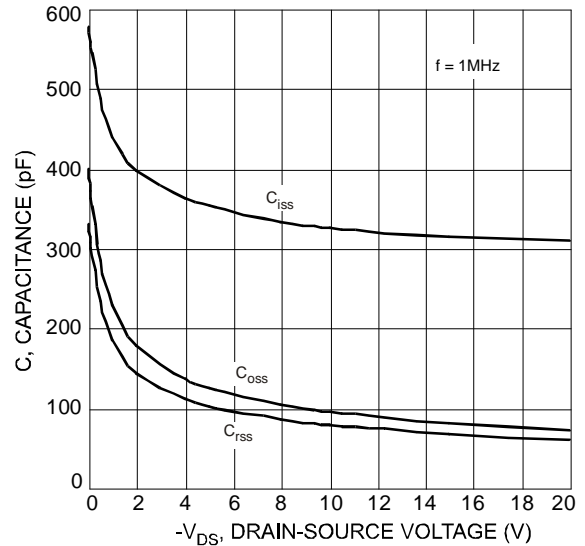


Fig. 6: Typical Capacitance

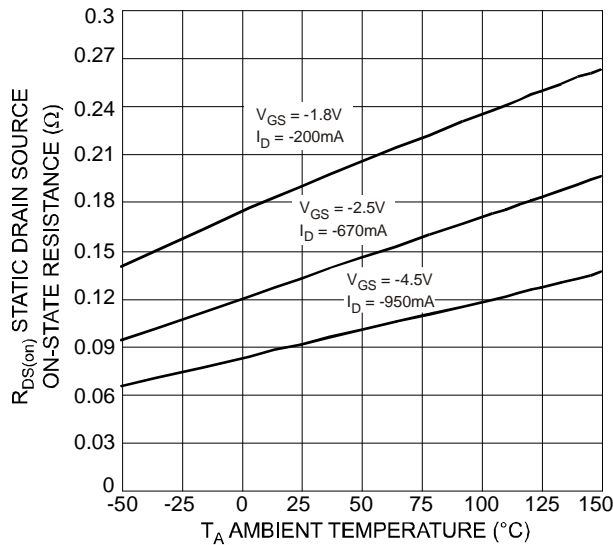


Fig. 7 Static Drain-Source On-State Resistance vs Ambient Temperature

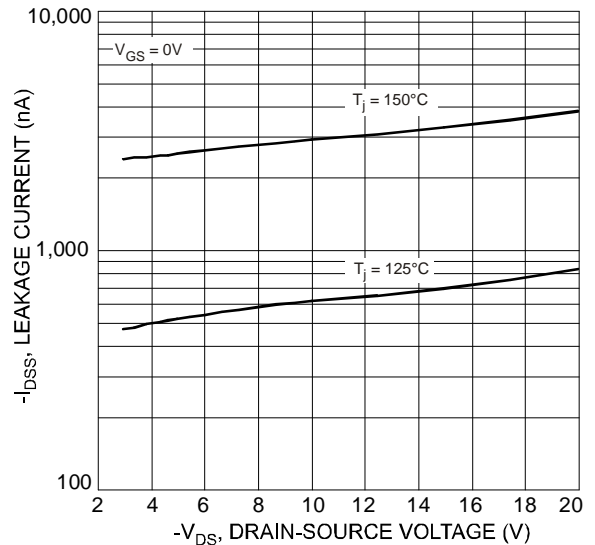


Fig. 8 Drain-Source Leakage Current vs Voltage

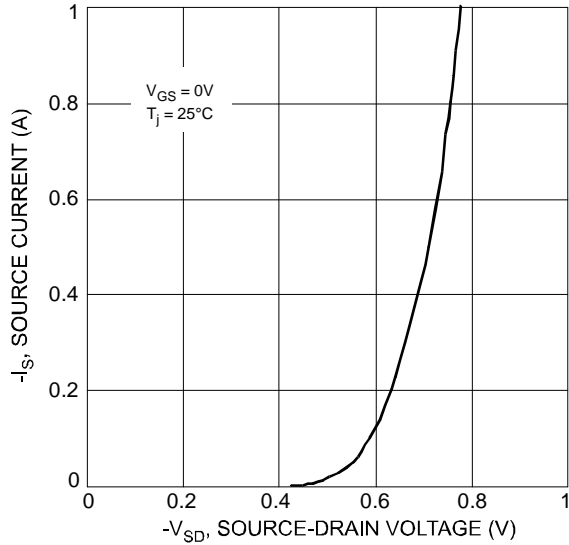
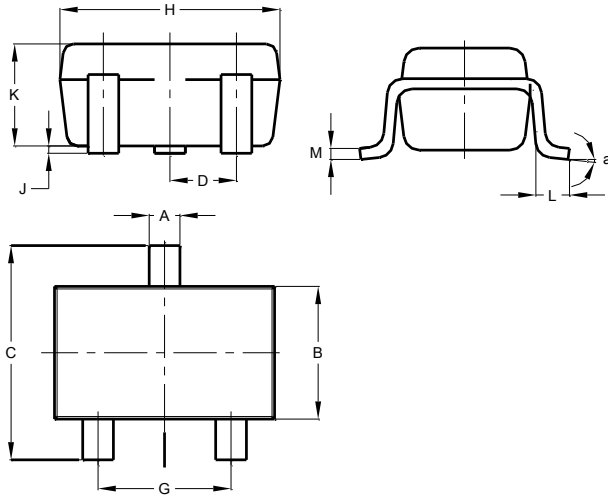


Fig. 9 Diode Forward Voltage vs. Current

**Package Outline Dimensions**

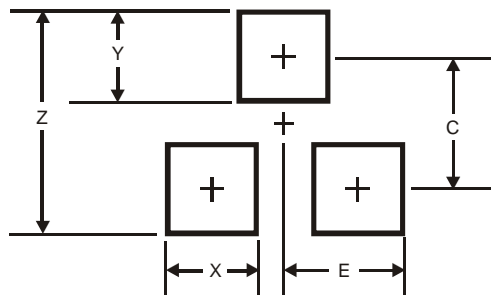
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for the latest version.



SOT323			
Dim	Min	Max	Typ
A	0.25	0.40	0.30
B	1.15	1.35	1.30
C	2.00	2.20	2.10
D	0.650 BSC		
F	0.375	0.475	0.425
G	1.20	1.40	1.30
H	1.80	2.20	2.15
J	0.00	0.10	0.05
K	0.90	1.00	0.95
L	0.25	0.40	0.30
M	0.10	0.18	0.11
a	8°C		
All Dimensions in mm			

**Suggested Pad Layout**

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



Dimensions	Value (in mm)
Z	2.8
X	0.7
Y	0.9
C	1.9
E	1.0

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